## **NEC**

# NPN SILICON POWER TRANSISTOR 2SC2518

**DESCRIPTION** 

The 2SC2518 is NPN triple diffused transistor designed for switching regulator, DC-DC converter and ultrasonic appliance ap-

plications.

**FEATURES** 

- High speed, high voltage switching.
- Low collector saturation voltage.
- Specified of reverse biased SOA with inductive loads.

#### **ABSOLUTE MAXIMUM RATINGS**

Maximum Temperatures

Storage Temperature					
Junction Temperature 150 °C Maximum					
Maximum Power Dissipation (T <sub>c</sub> = 25 °C)					
Total Power Dissipation					
Maximum Voltages and Currents( $T_a = 25$ °C)					
$V_{CBO}$	Collector to Base Voltage	500 V			
$V_{CEO}$	Collector to Emitter Voltage	400 V			
$V_{EBO}$	Emitter to Base Voltage	8.0 V			
IC(DC)	Collector Current (DC)	5.0 A			
I <sub>C (puise)</sub>	Collector Current (pulse)*	10 A			
IB(DC)	Base Current (DC)	2.5 A			
* PW ≤ 300 µs, Duty Cycle ≤ 10 %					

PACKAGE DIMENSIONS
in millimeters (inches)

10.7 MAX.
081 (0.421 MAX.) 3.6± 0.2 (0.193 MAX.)
0.0394) (√ φ 0.142) (0.093 MAX.)
1.3± 0.2 (0.051) (0.0051)
1.3± 0.2 (0.051) (0.0051)
1.3± 0.2 (0.051) (0.0051)
1.3± 0.2 (0.0051) (0.002) (0.002)
1.3± 0.3 (0.031) (0.01) (0.11)
1. Base (B)
2. Collector (C)
3. Emitter (E)
4. Fin (Collector)
JEDEC: TO-220AB

#### ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
ton	Turn On Time			1.0	μs	/ I <sub>C</sub> = 2.0 A, I <sub>B1</sub> = -I <sub>B2</sub> = 0.4 A
t <sub>stg</sub>	Storage Time			2.5	μs	$R_L = 75 \Omega$ , $V_{CC} = 150 V$
tf	Fall Time			0.7	μς	See Test Circuit.
hFE1	DC Current Gain**	20		80	_	$V_{CE} = 5.0 \text{ V, } I_{C} = 0.5 \text{ A}$
hFE2	DC Current Gain**	10 <sup>.</sup>			_	$V_{CF} = 5.0 \text{ V}, I_{C} = 2.0 \text{ A}$
VCE(sat)	Collector Saturation Voltage**			1.0	V	I <sub>C</sub> = 2.0 A, I <sub>B</sub> = 0.4 A
V <sub>BE(sat)</sub>	Base Saturation Voltage**			1.5	V	I <sub>C</sub> = 2.0 A, I <sub>B</sub> = 0.4 A
V <sub>CEO</sub> (SUS)	Collector to Emitter Sustaining Voltage	400			٧	I <sub>C</sub> = 2.0 A, I <sub>B</sub> = 0.4 A, L = 1 mH
VCEX(SUS)1	Collector to Emitter Sustaining Voltage	450			V	$I_C = 2.0 \text{ A}$ , $I_{B1} = -I_{B2} = 0.4 \text{ A}$ , $T_a = 125 ^{\circ}\text{C}$ , $L = 180 \mu\text{H}$ , Clamped
VCEX(SUS)2	Collector to Emitter Sustaining Voltage	400			V	$I_C = 4.0 \text{ A}, I_{B1} = 0.8 \text{ A}, -I_{B2} = 0.4 \text{ A},$ $T_a = 125 ^{\circ}\text{C}, L = 180 \mu\text{H}, Clamped$
ІСВО	Collector Cutoff Current			10	μΑ	V <sub>CB</sub> = 400 V, I <sub>E</sub> = 0
CER	Collector Cutoff Current			1.0	mA	$V_{CE} = 400 \text{ V}, R_{BE} = 51 \Omega, T_a = 125 ^{\circ}\text{C}$
ICEX1	Collector Cutoff Current			10	μΑ	$V_{CE} = 400 \text{ V}, V_{BE(OFF)} = -1.5 \text{ V}$
ICEX2	Collector Cutoff Current			1.0	mA	$V_{CE} = 400 \text{ V}, V_{BE(OFF)} = -1.5 \text{ V},$ $T_a = 125 ^{\circ}\text{C}$
<sup>I</sup> EBO	Emitter Cutoff Current			10	μΑ	V <sub>EB</sub> = 5.0 V, I <sub>C</sub> = 0

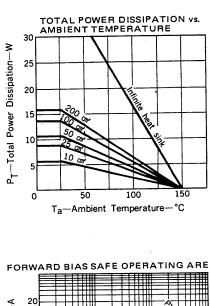
<sup>\*\*</sup>Pulse Test : PW  $\leq$  350  $\mu\text{s}$  , Duty Cycle  $\leq$  2 %/Pulsed

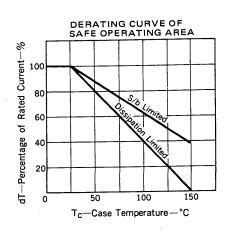
#### Classification of hFE1

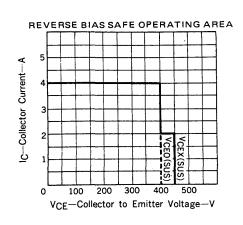
Rank	М	L	κ
Range	20 to 40	30 to 60	40 to 80

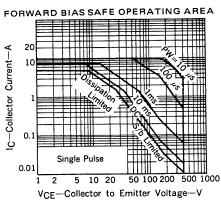
Test Conditions :  $V_{CE} = 5.0 \text{ V}$ ,  $I_{C} = 0.5 \text{ A}$ 

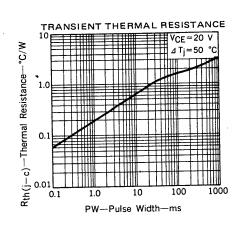
#### TYPICAL CHARACTERISTICS (Ta = 25 °C)

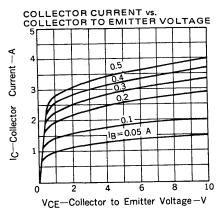


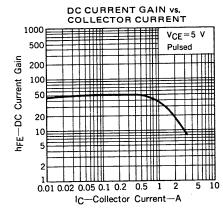


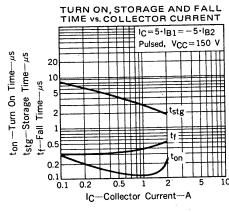


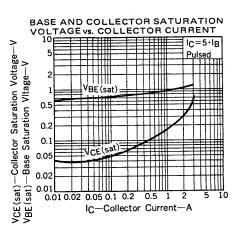












### SWITCHING TIME $(t_{on,}\,t_{stg,}\,t_f)$ TEST CIRCUIT

